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## 2N5410 (#23815)

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### Overview

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.60	V
DC Current Gain	HFE	40.00		120.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			80.00	V
Collector Current (dc)	$I_C$			5.00	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			80.00	V
Emitter-Base Voltage (Collector Open)	$V_{EBO}$			6.00	V
Power Dissipation, Total	$P_T$			52.00	W

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